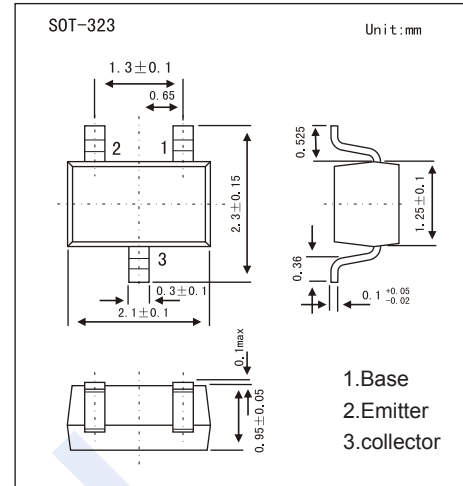


PNP Transistors

KTA2015

■ Features

- Excellent hFE Linearity
- Complementary to KTC4076



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-35	V
Collector - Emitter Voltage	V _{CEO}	-30	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _c	-500	mA
Base Current	I _B	-50	
Collector Power Dissipation	P _C	100	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 uA, I _E =0	-35			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B =0	-30			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 uA, I _c =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -35V, I _E =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _c =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-100mA, I _B =-10mA			-0.25	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =-100mA, I _B =-10mA			-1.2	
Base - emitter voltage	V _{BE}	V _{CE} = -1V, I _c = -100mA			-1	
DC current gain	h _{FE}	V _{CE} = -1V, I _c = -100mA	70		240	
		V _{CE} = -1V, I _c = -400mA	O	25		
			Y	40		
Collector output capacitance	C _{ob}	V _{CB} = -6V, f=1MHz		13		pF
Transition frequency	f _T	V _{CE} = -10V, I _c = -20mA		200		MHz

■ Classification of h_{FE}(1)

Type	KTA2015-O	KTA2015-Y
Range	70- 140	120-240
Mark'ng	ZO	ZY

PNP Transistors

KTA2015

■ Typical Characteristics

